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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

2 0 0 0 0 0	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101jcafa-x0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.3.7 40-pin products

• 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)





Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to $V_{ss.}$



1.5.12 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

^{3.} When setting to PIOR = 1

lt a	m	40	nin	11	nin	10	nin	EO	nin	64	(2) nin
Ite		40-			-pin		-pin	52	-pin I		-pin
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Clock output/buzz	er output	:	2		2		2		2		2
·		(Main s • 256 Hz	system clo z, 512 Hz,	оск: fмаin = 1.024 kHz	20 MHz c z, 2.048 kH	. ,	Hz, 8.192		884 kHz, 32	2.768 kHz	
8/10-bit resolution	A/D converter	9 channels 10 channels 10 channels 12 channels 12 channels									
Serial interface		[40-pin, 44-pin products]									
		 CSI: 1 channel/simplified l²C: 1 channel/UART: 1 channel CSI: 1 channel/simplified l²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [48-pin, 52-pin products] CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel CSI: 1 channel/simplified l²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [64-pin products] CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel 									
	I ² C bus	1 channe		1 channe		1 channe		1 channe	J LIN-bus):	1 channe	
Multiplier and divid		 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 									
		 16 bits × 16 bits + 32 bits = 32 bits (Unsigned) 									
DMA controller		2 channe	ls								
Vectored	Internal	2	27	:	27	2	27		27	2	27
interrupt sources	External		7		7		10		12		13
Key interrupt			4		4		6		8		8
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution ^{Note} Internal reset by RAM parity error Internal reset by illegal-memory access 									
Power-on-reset ci	rcuit	 Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.) 									
Voltage detector		Rising edge : 1.67 V to 4.06 V (14 stages) Falling edge : 1.63 V to 3.98 V (14 stages)									
On-chip debug fur	nction	Provided									
Power supply volta	$V_{DD} = 1.6 \text{ to } 5.5 \text{ V} (T_{A} = -40 \text{ to } +85^{\circ}\text{C})$ $V_{DD} = 2.4 \text{ to } 5.5 \text{ V} (T_{A} = -40 \text{ to } +105^{\circ}\text{C})$										
Operating ambien	$T_A = 40$ to +85°C (A: Consumer applications, D: Industrial applications) $T_A = 40$ to +105°C (G: Industrial applications)										

<R>

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

							(1/2)				
	Item	80-	•	100)-pin	128	-pin				
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx				
Code flash m	emory (KB)	96 te	o 512	96 t	o 512	192	to 512				
Data flash me	emory (KB)	8	_	8	-	8	-				
RAM (KB)		8 to 3	2 Note 1	8 to 3	32 Note 1	16 to 5	32 Note 1				
Address space	e	1 MB									
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	K1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)								
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)									
Subsystem cl	ock	XT1 (crystal) os 32.768 kHz	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS)								
Low-speed or	n-chip oscillator	15 kHz (TYP.)									
General-purp	ose register	(8-bit register ×	8) \times 4 banks								
Minimum instruction execution time		0.03125 <i>μ</i> s (Hig	h-speed on-chip	oscillator: fin = 3	32 MHz operation)					
		0.05 <i>µ</i> s (High-s	peed system clo	ck: fмx = 20 MHz	operation)						
		30.5 <i>µ</i> s (Subsys	stem clock: fsue =	- 32.768 kHz ope	eration)						
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 									
I/O port	Total	7	74		92	1	20				
	CMOS I/O	(N-ch O.D. I/O	64 [EV _{DD} withstand le]: 21)	(N-ch O.D. I/O	82 [EV⊳⊳ withstand ge]: 24)	(N-ch O.D. I/O	10 [EV _{DD} withstand ge]: 25)				
	CMOS input		5		5		5				
	CMOS output		1		1		1				
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4				
Timer	16-bit timer	12 cha	annels	12 ch	annels	16 ch	annels				
	Watchdog timer	1 cha	annel	1 ch	annel	1 cha	annel				
	Real-time clock (RTC)	1 cha	annel	1 ch	annel	1 cha	annel				
	12-bit interval timer (IT)	1 cha	annel	1 ch	annel	1 cha	annel				
	Timer output	12 channels 12 channels (PWM outputs: 10 ^{Note 2}) (PWM outputs: 10 ^{Note 2})				16 channels (PWM outputs:	14 Note 2)				
	RTC output	1 channel • 1 Hz (subsyster)	tem clock: fsuв =								

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library** for RL78 Family (R20UT2944).



- **Notes 1.** Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz

2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

LS (low-speed main) mode: $1.8~V \leq V_{\text{DD}} \leq 5.5~V @\,1$ MHz to 8 MHz

LV (low-voltage main) mode: 1.6 V \leq V_DD \leq 5.5 V@1 MHz to 4 MHz

- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Items	Symbol		Conditions	;	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсү	Main	HS (high-	$2.7V {\le} V_{DD} {\le} 5.5V$	0.03125		1	μS
instruction execution time)		system clock (fmain)	speed main) mode	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
		operation	LS (low-speed main) mode	$1.8V\!\le\!V_{DD}\!\le\!5.5V$	0.125		1	μS
			LV (low- voltage main) mode	$1.6 V \le V_{DD} \le 5.5 V$	0.25		1	μS
		Subsystem of operation	clock (fsuв)	$1.8 V \! \le \! V_{DD} \! \le \! 5.5 V$	28.5	30.5	31.3	μS
		In the self	HS (high-	$2.7V{\leq}V_{\text{DD}}{\leq}5.5V$	0.03125		1	μS
		programming mode	speed main) mode	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μS
			LS (low-speed main) mode	$1.8V\!\leq\!V_{DD}\!\leq\!5.5V$	0.125		1	μS
			LV (low- voltage main) mode	$1.8 V \le V_{DD} \le 5.5 V$	0.25		1	μS
External system clock	fex	$2.7 \text{ V} \leq \text{V}_{DD} \leq$		1	1.0		20.0	MHz
frequency		2.4 V ≤ V _{DD} <			1.0		16.0	MHz
		1.8 V ≤ V _{DD} <			1.0		8.0	MHz
		1.6 V ≤ V _{DD} <			1.0		4.0	MHz
	fexs				32		35	kHz
External system clock input	texh, texl	$2.7 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$						ns
high-level width, low-level width		2.4 V ≤ V _{DD} <			24 30			ns
		1.8 V ≤ V _{DD} <			60			ns
		1.6 V ≤ V _{DD} <			120			ns
	texhs, texls				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтıн, tтı∟				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	fтo	HS (high-spe	eed 4.0 V	$\leq EV_{DD0} \leq 5.5 V$			16	MHz
output frequency		main) mode		\leq EV _{DD0} < 4.0 V			8	MHz
			1.8 V	\leq EV _{DD0} < 2.7 V			4	MHz
			1.6 V	≤ EV _{DD0} < 1.8 V			2	MHz
		LS (low-spee	ed 1.8 V	$\leq EV_{DD0} \leq 5.5 V$			4	MHz
		main) mode	1.6 V	≤ EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta main) mode	age 1.6 V	$\leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			2	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-spe	eed 4.0 V	$\leq EV_{DD0} \leq 5.5 V$			16	MHz
frequency		main) mode	2.7 V	\leq EV _{DD0} < 4.0 V			8	MHz
			1.8 V	\leq EV _{DD0} < 2.7 V			4	MHz
			1.6 V	$\leq EV_{DD0} < 1.8 V$			2	MHz
		LS (low-spee	ed 1.8 V	$\leq EV_{DD0} \leq 5.5 V$			4	MHz
		main) mode	1.6 V	$\leq EV_{DD0} < 1.8 V$			2	MHz
		LV (low-volta	age 1.8 V	$\leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			4	MHz
		main) mode	1.6 V	\leq EV _{DD0} < 1.8 V			2	MHz
Interrupt input high-level width,	tintн,	$INTP0 1.6 V \le V_{DD} \le 5.5 V$			1			μS
low-level width	tintl	INTP1 to INT	[P11 1.6 V	$\leq EV_{DD0} \leq 5.5 V$	1			μS
Key interrupt input low-level	tкв	KR0 to KR7	1.8 V	$\leq EV_{DD0} \leq 5.5 V$	250			ns
width			1.6 V	$\leq EV_{DD0} < 1.8 V$	1			μS
RESET low-level width	trsl				10			μS

(Note and Remark are listed on the next page.)





TCY vs VDD (LS (low-speed main) mode)



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	(Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY1	tксү1 \geq 2/fclк	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$	62.5		250		500		ns
			$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	83.3		250		500		ns
SCKp high-/low-level width	tĸнı, tĸ∟ı	$4.0 V \le EV_{DI}$	$500 \leq 5.5 \text{ V}$	tксү1/2 – 7		tксү1/2 – 50		tксү1/2 – 50		ns
		2.7 V ≤ EV _D	$500 \leq 5.5 \text{ V}$	tксү1/2 – 10		tксү1/2 – 50		tксү1/2 – 50		ns
SIp setup time (to SCKp [↑])	tsik1	$4.0 \ V \le EV_{DI}$	$00 \leq 5.5 \text{ V}$	23		110		110		ns
Note 1		$2.7 \text{ V} \leq EV_{\text{DI}}$	$00 \leq 5.5 \text{ V}$	33		110		110		ns
Slp hold time (from SCKp↑) ^{Note 2}	tksii	$2.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$500 \leq 5.5 \text{ V}$	10		10		10		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 20 pF ^{Not}	te 4		10		10		10	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V})$

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** This value is valid only when CSI00's peripheral I/O redirect function is not used.
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 g: PIM and POM numbers (g = 1)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2) ($T_A = -40$ to $+85^{\circ}$ C, 1.6 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Condit	ions		h-speed Mode		/-speed Mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY2	$4.0~V \leq EV_{DD0} \leq 5.5$	20 MHz < fмск	8/fмск		_		_		ns
Note 5		V	fмск \leq 20 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.7~V \leq EV_{\text{DD0}} \leq 5.5$	16 MHz < fмск	8/fмск		_		_		ns
		V	fмск \leq 16 MHz	6/fмск		6/fмск		6/fмск		ns
	$2.4 \ V \leq EV_{\text{DD0}}$			6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		$1.8~V \le EV_{DD0} \le 5.5~V$		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
	$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns	
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$	V	—		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tкн2, tкL2	$4.0~V \le EV_{DD0} \le 5.5~V$		tксү2/2 – 7		tксү2/2 - 7		tксү2/2 - 7		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$		tксү2/2 – 8		tксү2/2 - 8		tксү2/2 - 8		ns
		$1.8~V \le EV_{DD0} \le 5.5~V$		tксү2/2 – 18		tксү2/2 – 18		tксү2/2 – 18		ns
		$1.7~V \leq EV_{DD0} \leq 5.5~V$		tксү2/2 – 66		tксү2/2 - 66		tксү2/2 - 66		ns
	$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$		V	_		tксү2/2 - 66		tксү2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)



Parameter	Symbol		Conditions		speed	high- main) ode		/-speed Mode	LV (low- voltage main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 4}$		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2) (T_A = -40 to +85°C. 1.8 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V. Vss = EV_{SS0} = EV_{SS1} = 0 V)

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

 $2.4~V \leq EV_{\text{DD0}} < 2.7~V$: MAX. 2.6 Mbps

 $1.8~V \leq EV_{\text{DD0}} < 2.4~V$: MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq V_{DD} \leq 5.5 V)

LV (low-voltage main) mode: $4 \text{ MHz} (1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** $V_{b}[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



			$\sqrt{DD0} = EVDD1 \le VDD \le$				LS (low-		LV (low-		Unit
Parameter	Symbol		Conditions			high-					Unit
						main) ode	speed	main) ode		age Mode	
								1			
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$			Note		Note		Note	bps
			$2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$			1		1		1	
				Theoretical		2.8		2.8		2.8	Mbps
				value of the		Note 2		Note 2		Note 2	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$1.4 \text{ k}\Omega, V_{\text{b}} = 2.7$							
				V							
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$			Note		Note		Note	bps
			$2.3~V \leq V_b \leq 2.7~V$			3		3		3	
				Theoretical		1.2		1.2		1.2	Mbps
				value of the		Note 4		Note 4		Note 4	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$2.7 \text{ k}\Omega$, V _b = 2.3							
				V							
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$			Notes		Notes		Notes	bps
			$1.6~V \leq V_b \leq 2.0~V$			5, 6		5, 6		5, 6	
				Theoretical		0.43		0.43		0.43	Mbps
				value of the		Note 7		Note 7		Note 7	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$5.5 \text{ k}\Omega, \text{V}_{\text{b}} = 1.6$							
				V							

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2) (TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Notes 1. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV $_{DD0} \leq$ 5.5 V and 2.7 V \leq V $_{b} \leq$ 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.



CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fмск: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



(3) I²C fast mode plus

 $(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = EV_{SS0} = EV_{SS1} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions		h-speed Mode	LS (low main)	/-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: fc∟κ≥ 10 MHz	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	1000		_	_	_	kHz
Setup time of restart condition	tsu:sta	$2.7 V \leq EV_{DD0} \leq 5.8$	$7 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			—		_	-	μS
Hold time ^{Note 1}	thd:sta	$2.7 V \le EV_{DD0} \le 5.8$	$7 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			_		_	_	μS
Hold time when SCLA0 = "L"	t∟ow	$2.7 V \leq EV_{DD0} \leq 5.8$	$7~V \leq EV_{\text{DD0}} \leq 5.5~V$			—		_		μS
Hold time when SCLA0 = "H"	tніgн	$2.7 V \leq EV_{DD0} \leq 5.5$	5 V	0.26		_	_	_	-	μS
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.9$	5 V	50		_	_	_	_	μS
Data hold time (transmission) ^{Note 2}	thd:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.9$	5 V	0	0.45	_	_	_	_	μS
Setup time of stop condition	tsu:sto	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.9$	$.7~V \leq EV_{\text{DD0}} \leq 5.5~V$			_	_	_	_	μS
Bus-free time	tвuғ	$2.7 V \le EV_{DD0} \le 5.8$	5 V	0.5		_	_	-	_	μS

<R>

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: $C_b = 120 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1



Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD2	HALT	HS (high-	fin = 32 MHz ^{Note 4}	$V_{DD} = 5.0 V$		0.54	2.90	mA
Current	Note 2	mode	speed main) mode ^{Note 7}		V _{DD} = 3.0 V		0.54	2.90	mA
				fin = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	2.30	mA
					V _{DD} = 3.0 V		0.44	2.30	mA
				$f_{IH} = 16 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 V$		0.40	1.70	mA
					V _{DD} = 3.0 V		0.40	1.70	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{Note 3}$,	Square wave input		0.28	1.90	mA
			speed main) mode ^{Note 7}	$V_{DD} = 5.0 V$	Resonator connection		0.45	2.00	mA
				$f_{MX} = 20 \text{ MHz}^{Note 3}$,	Square wave input		0.28	1.90	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.45	2.00	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.19	1.02	mA
				$V_{DD} = 5.0 V$	Resonator connection		0.26	1.10	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.19	1.02	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.26	1.10	mA
		Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μA	
			clock	$T_A = -40^{\circ}C$	Resonator connection		0.44	0.76	μA
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μA
				$T_A = +25^{\circ}C$	Resonator connection		0.49	0.76	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.37	1.17	μA
				$T_A = +50^{\circ}C$	Resonator connection		0.56	1.36	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.53	1.97	μA
				$T_A = +70^{\circ}C$	Resonator connection		0.72	2.16	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.82	3.37	μA
				$T_A = +85^{\circ}C$	Resonator connection		1.01	3.56	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		3.01	15.37	μA
				$T_A = +105^{\circ}C$	Resonator connection		3.20	15.56	μA
	DD3 ^{Note 6}	STOP	$T_{\text{A}} = -40^{\circ}C$				0.18	0.50	μA
		mode ^{Note 8}	$T_A = +25^{\circ}C$				0.23	0.50	μA
			T _A = +50°C				0.30	1.10	μA
			$T_A = +70^{\circ}C$				0.46	1.90	μA
			$T_A = +85^{\circ}C$	с			0.75	3.30	μA
		-	T _A = +105°C	;			2.94	15.30	μA

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (TA = -40 to $+105^{\circ}$ C, 2.4 V $\leq EV_{DD0} \leq V_{DD} \leq 5.5$ V, Vss = EVss₀ = 0 V) (2/2)

(Notes and Remarks are listed on the next page.)



Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
 - r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14),
 h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m

= 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

Parameter	Symbol		Condit	ions	HS (high-spee	ed main) Mode	Unit
					MIN.	MAX.	
Transfer rate		Transmission	$4.0~V \leq EV_{\text{DD0}} \leq 5.5$			Note 1	bps
			V, $2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate		2.6 Note 2	Mbps
				$\begin{array}{l} C_{b}=50 \; pF, \; R_{b}=1.4 \; k\Omega, \; V_{b}=2.7 \\ V \end{array} \label{eq:cb}$			
		$2.7 \ V \leq EV_{\text{DD0}} < 4.0$			Note 3	bps	
			V, $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3$		1.2 Note 4	Mbps
			2.4 V ≤ EV _{DD0} < 3.3	V		Note 5	bps
			V, $1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6$ V		0.43 Note 6	Mbps

Notes 1. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV _DD0 \leq 5.5 V and 2.7 V \leq V _b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions		HS (high-spee	Unit	
				MIN.	MAX.	
SCKp cycle time ^{Note 1}	t ксү2	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \\ V, \end{array}$	24 MHz < fмск	28/f мск		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	24/f мск		ns
		$2.7 \: V {\le} V_b {\le} 4.0 \: V$	$8 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	20/f мск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	16/f мск		ns
			fмск \leq 4 MHz	12/f мск		ns
		$\begin{array}{l} 2.7 \ V \leq E V_{DD0} < 4.0 \\ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	24 MHz < fмск	40/f мск		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	32/f мск		ns
			$16 \text{ MHz} < f_{MCK} \le 20 \text{ MHz}$	28/f мск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	24/fмск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	16/f мск		ns
			fмск \leq 4 MHz	12/f мск		ns
		$2.4~V \leq EV_{DD0} < 3.3$	24 MHz < fмск	96/f мск		ns
		V,	$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	72/f мск		ns
		$1.6 V \le V_b \le 2.0 V$	$16 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	64/f мск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	52/f мск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	32/f мск		ns
			fмск \leq 4 MHz	20/fмск		ns
SCKp high-/low-level width	tĸ∟2 -			tkcy2/2 - 24		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		tkcy2/2 - 36		ns
		$\label{eq:VD0} \begin{array}{l} 2.4 \ V \leq EV_{D00} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{array}$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) ^{Note2}	2 2 2 2	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$		1/fмск + 40		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		1/fмск + 40		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{№te 3}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output ^{Note 4}	tkso2	$ \begin{split} 4.0 \ V &\leq EV_{\text{DD0}} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{split} $			2/fмск + 240	ns
		$\label{eq:V_b_b_b_b_b_b_b} \begin{split} 2.7 \ V &\leq EV_{\text{DD0}} < 4.0 \ \text{V}, \ 2.3 \ \text{V} \leq V_b \leq 2.7 \ \text{V}, \\ C_b &= 30 \ \text{pF}, \ R_b = 2.7 \ \text{k}\Omega \end{split}$			2/fмск + 428	ns
			3 V, 1.6 V \leq Vb \leq 2.0 V		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00, 01, 02, 10, 12, 13)



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{V}_{\text{BGR}}^{\text{Note 3}}, \text{ Reference voltage (-)} = \text{AV}_{\text{REFM}}^{\text{Note 4}} = 0 \text{ V}, \text{ HS (high-speed main) mode)}$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	t CONV	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN			0		$V_{\text{BGR}}{}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = Vss, the MAX. values are as follows. Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = -40 to $+105^{\circ}$ C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μS



C₂

4.5 32-pin Products

R5F100BAANA, R5F100BCANA, R5F100BDANA, R5F100BEANA, R5F100BFANA, R5F100BGANA R5F101BAANA, R5F101BCANA, R5F101BDANA, R5F101BEANA, R5F101BFANA, R5F101BGANA R5F100BADNA, R5F100BCDNA, R5F100BDDNA, R5F100BEDNA, R5F100BFDNA, R5F100BGDNA R5F101BADNA, R5F101BCDNA, R5F101BDDNA, R5F101BEDNA, R5F101BFDNA, R5F101BGDNA R5F100BAGNA, R5F100BCGNA, R5F100BDGNA, R5F100BEGNA, R5F100BFGNA, R5F100BGGNA

JEITA Package code	RENESAS code	Previous code	MASS (TYP.)[g]
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-5	0.06





A₁





Referance	Dimens	ension in Millimeters			
Symbol	Min	Nom	Max		
D	4.95	5.00	5.05		
E	4.95	5.00	5.05		
А			0.80		
A ₁	0.00				
b	0.18	0.25	0.30		
е		0.50			
Lp	0.30	0.40	0.50		
х			0.05		
у			0.05		
ZD		0.75			
Z _E		0.75	—		
C2	0.15	0.20	0.25		
D ₂		3.50			
E ₂		3.50			

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R01DS0131EJ0330 Rev.3.30 Mar 31, 2016

